

FDJ1027P

P-Channel 1.8V Specified PowerTrench® MOSFET

Features

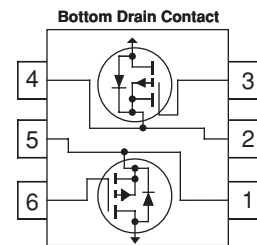
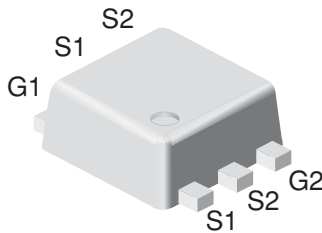
- -2.8 A, -20 V $R_{DS(ON)} = 160\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$
 $R_{DS(ON)} = 230\text{ m}\Omega @ V_{GS} = -2.5\text{ V}$
 $R_{DS(ON)} = 390\text{ m}\Omega @ V_{GS} = -1.8\text{ V}$
- Low gate charge, High Power and Current handling capability
- High performance trench technology for extremely low $R_{DS(ON)}$
- FLMP SC75 package: Enhanced thermal performance in industry-standard package size

General Description

This dual P-Channel 1.8V specified MOSFET uses Fairchild's advanced low voltage PowerTrench process. Packaged in FLMP SC75, the $R_{DS(ON)}$ and thermal properties of the device are optimized for battery power management applications.

Applications

- Battery management/Charger Application
- Load switch



MOSFET Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 8	V
I_D	Drain Current – Continuous (Note 1a)	-2.8	A
		-12	
P_D	Power Dissipation for Single Operation (Note 1a) (Note 1b)	1.5	W
		0.9	
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$
Thermal Characteristics			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	80	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	5	

Package Marking and Ordering Information

.G	FDJ1027P	7"	8mm	3000 units
----	----------	----	-----	------------

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

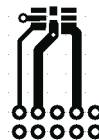
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		-13		$\text{mV}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
I_{GSS}	Gate-Body Leakage	$V_{GS} = \pm 8\text{ V}, V_{DS} = 0\text{ V}$			± 100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.4	-0.8	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		3		$\text{mV}/^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -4.5\text{ V}, I_D = -2.8\text{ A}$ $V_{GS} = -2.5\text{ V}, I_D = -2.2\text{ A}$ $V_{GS} = -1.8\text{ V}, I_D = -1.7\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -2.8\text{ A}, T_J = 125^\circ\text{C}$		108 163 283 150	160 230 390 238	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -2.8\text{ A}$		5		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		290		pF
C_{oss}	Output Capacitance			55		pF
C_{rss}	Reverse Transfer Capacitance			29		pF
R_g	Gate Resistance	$f = 1.0\text{ MHz}$		13		Ω
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -10\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$		8	16	ns
t_r	Turn-On Rise Time			13	23	ns
$t_{d(off)}$	Turn-Off Delay Time			13	23	ns
t_f	Turn-Off Fall Time			18	32	ns
Q_g	Total Gate Charge	$V_{DS} = -10\text{ V}, I_D = -2.8\text{ A},$ $V_{GS} = -4.5\text{ V}$		3	4	nC
Q_{gs}	Gate-Source Charge			0.65		nC
Q_{gd}	Gate-Drain Charge			0.75		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current				-1.25	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -1.25\text{ A}$ (Note 2)		-0.8	-1.2	V
t_{rr}	Diode Reverse Recovery Time	$I_F = -2.8\text{ A},$ $d_{IF}/d_t = 100\text{ A}/\mu\text{s}$		14		ns
Q_{rr}	Diode Reverse Recovery Charge			4		nC

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $80^\circ\text{C}/\text{W}$ when mounted on a 1in^2 pad of 2 oz copper (Single Operation).



b) $140^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper (Single Operation).

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width < $300\ \mu\text{s}$, Duty Cycle < 2.0%

Typical Characteristics

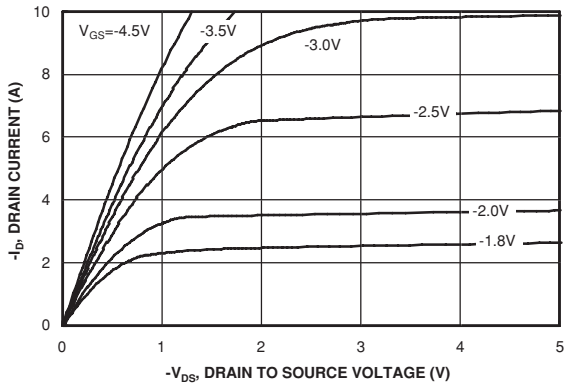


Figure 1. On-Region Characteristics.

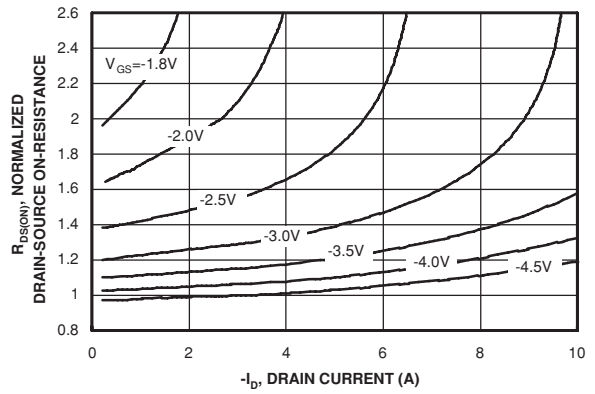


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

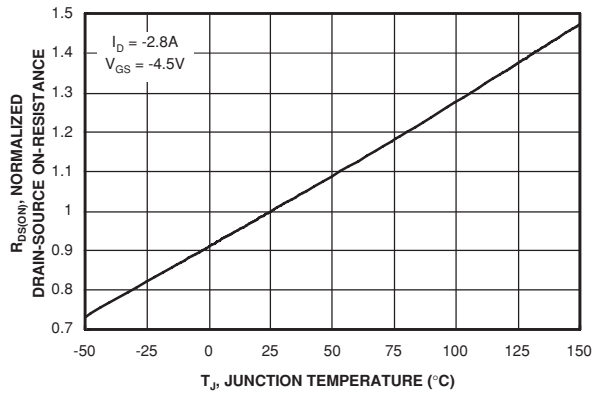


Figure 3. On-Resistance Variation with Temperature.

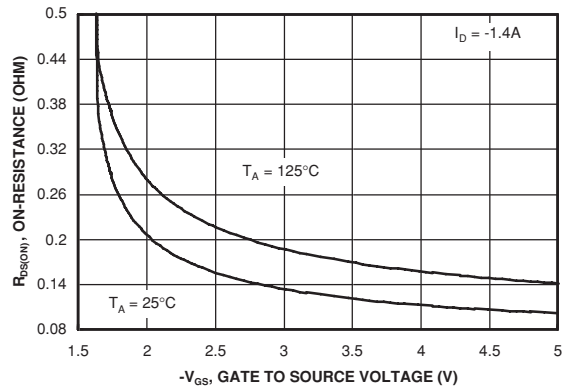


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

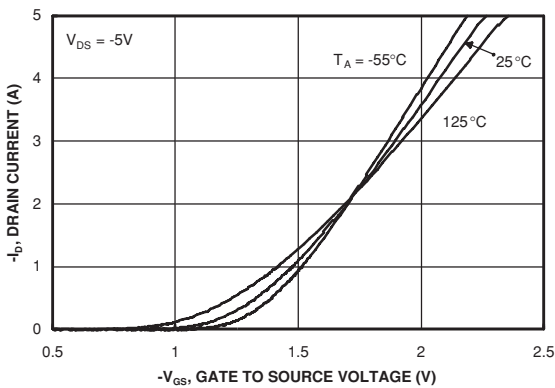


Figure 5. Transfer Characteristics.

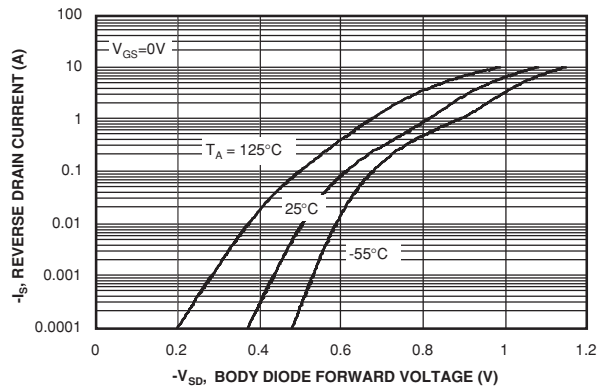


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

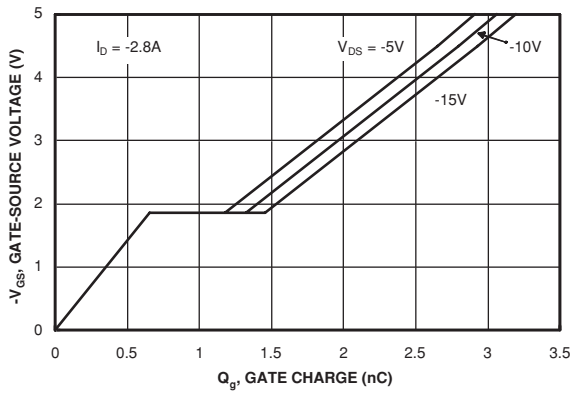


Figure 7. Gate Charge Characteristics.

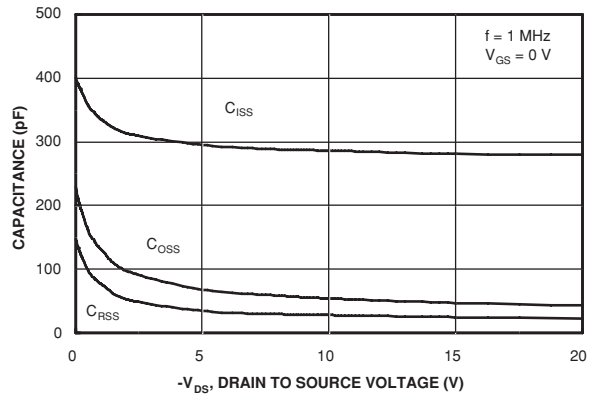


Figure 8. Capacitance Characteristics.

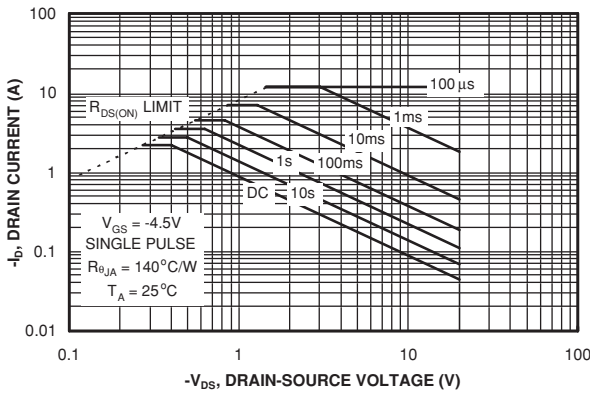


Figure 9. Maximum Safe Operating Area.

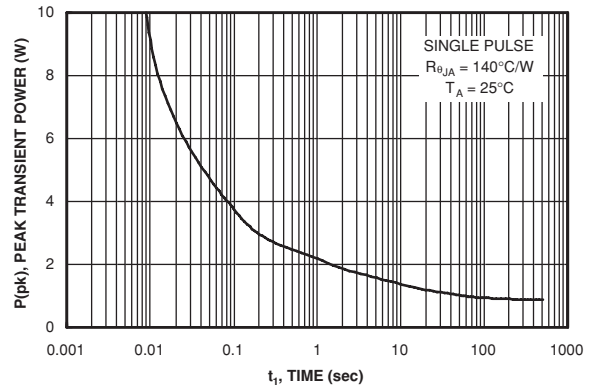


Figure 10. Single Pulse Maximum Power Dissipation.

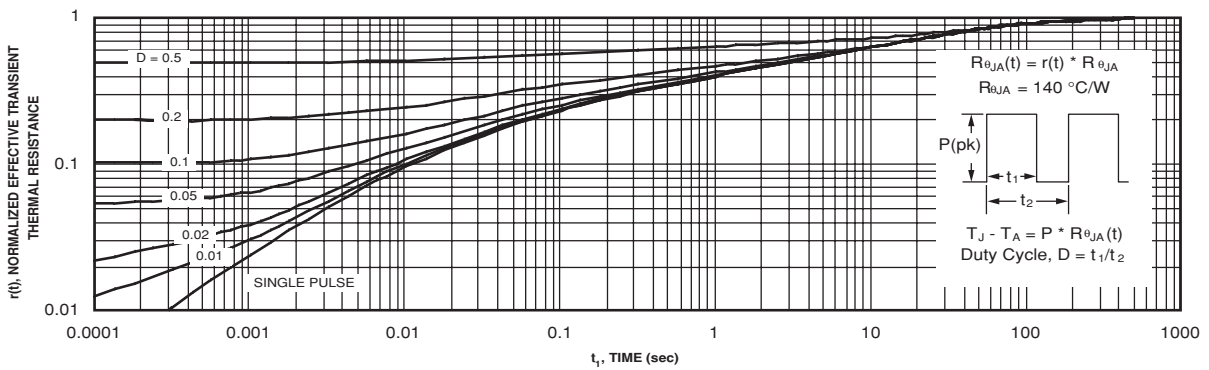
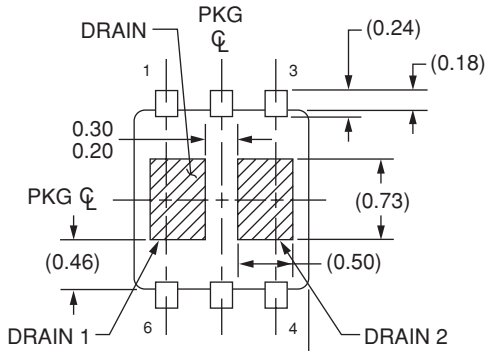


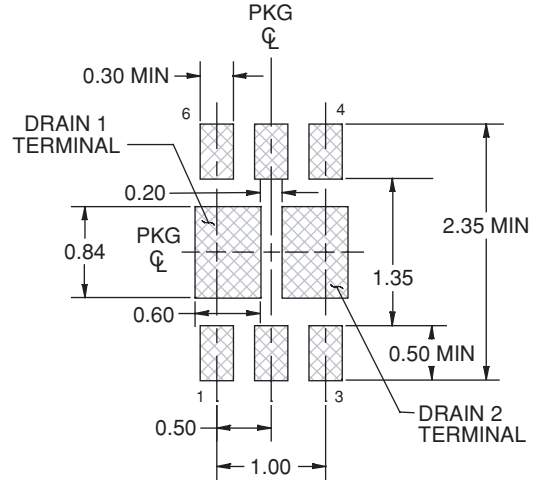
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

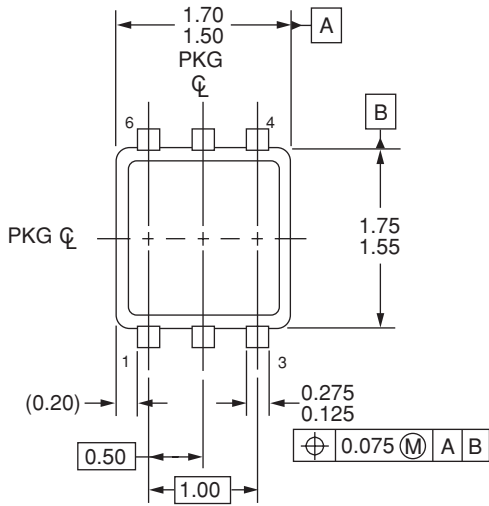
Dimensional Outline and Pad Layout



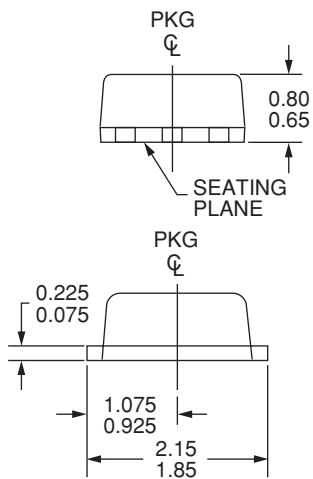
Bottom View



Recommended Landing Pattern



Top View



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE ^x TM	FACT Quiet Series TM	OCX TM	SILENT SWITCHER [®]	UniFET TM
ActiveArray TM	GlobalOptoisolator TM	OCXPro TM	SMART START TM	UltraFET [®]
Bottomless TM	GTO TM	OPTOLOGIC [®]	SPM TM	VCX TM
Build it Now TM	HiSeC TM	OPTOPLANAR TM	Stealth TM	Wire TM
CoolFET TM	I ² C TM	PACMAN TM	SuperFET TM	
CROSSVOLT TM	<i>i-Lo</i> TM	POP TM	SuperSOT TM -3	
DOMET TM	ImpliedDisconnect TM	Power247 TM	SuperSOT TM -6	
EcoSPARK TM	IntelliMAX TM	PowerEdge TM	SuperSOT TM -8	
E ² CMOS TM	ISOPLANAR TM	PowerSaver TM	SyncFET TM	
EnSigna TM	LittleFET TM	PowerTrench [®]	TCM TM	
FACT TM	MICROCOUPLER TM	QFET [®]	TinyBoost TM	
FAST [®]	MicroFET TM	QS TM	TinyBuck TM	
FAST _r TM	MicroPak TM	QT Optoelectronics TM	TinyPWM TM	
FPS TM	MICROWIRE TM	Quiet Series TM	TinyPower TM	
FRFET TM	MSX TM	RapidConfigure TM	TinyLogic [®]	
	MSXPro TM	RapidConnect TM	TINYOPTO TM	
Across the board. Around the world. TM		μSerDes TM	TruTranslation TM	
The Power Franchise [®]		ScalarPump TM	UHC TM	
Programmable Active Droop TM				

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
- A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.